[Summary of the Invention]

[Problems to be Solved by the Invention]

[0005]

An object of the present invention is to provide an evaporation material for use in a vacuum deposition method capable of suppressing the bumping phenomenon upon melting the evaporation material.

[Means for Solving the Problems]

[0006]

In order to achieve the foregoing object, the first embodiment of the present invention provides an evaporation material for use in a vacuum deposition method, wherein the evaporation material ~~comprises~~ consists of one or more types among Au, Ag, Pt, Pd and their alloys, micropores are formed on a surface of the evaporation material, and a number of the micropores having an equivalent circle diameter of 0.1 μm or more and 10.0 μm or less is one or more micropores per 500 μm^2. Moreover, the second embodiment of the present invention provides an evaporation material for use in a vacuum deposition method, wherein the evaporation material ~~comprises~~ consists of one or more types among Au, Ag, Pt, Pd and their alloys, and a hydrogen content in the evaporation material is 10 wtppm or less.

[Effect of the Invention]

[0007]

According to the present invention, it is possible to suppress the bumping phenomenon upon melting the evaporation material, and thereby reduce the particles that become adhered on the substrate. Accordingly, the present invention is able to contribute to improving the yield of products.

[Brief Description of the Drawings]

[0008]

[Fig. 1]

Fig. 1 is an image obtained from observing the surface of the evaporation material of Conventional Example 1 using an SEM (5000X).

[Fig. 2]

Fig. 2 is an image obtained from observing the surface of the evaporation material of Example 1-1 using an SEM (5000X).

[Fig. 3]

CLAIMS

[Claim 1]

An evaporation material, wherein the evaporation material ~~comprises~~ consists of one or more types among Au, Ag, Pt, Pd and their alloys, micropores are formed on a surface of the evaporation material, and a number of the micropores having an equivalent circle diameter of 0.1 μm or more and 10.0 μm or less is one or more micropores per 500 μm^2.

[Claim 2]

The evaporation material according to claim 1, wherein a purity of the evaporation material is 3N (99.9 wt%) or higher.

~~[Claim 3]~~

~~An evaporation material, wherein the evaporation material comprises one or more types among Au, Ag, Pt, Pd and their alloys, and a hydrogen content in the evaporation material is 10 wtppm or less.~~

~~[Claim 4]~~

~~The evaporation material according to claim 3, wherein a carbon content in the evaporation material is 10 wtppm or less.~~

~~[Claim 5]~~

~~The evaporation material according to claim 3 or claim 4, wherein an oxygen content in the evaporation material is 100 wtppm or less.~~

~~[Claim 6]~~

~~The evaporation material according to any one of claims 3 to 5, wherein a total content of sulfur and phosphorus in the evaporation material is 10 wtppm or less.~~

~~[Claim 7]~~

~~A method of producing the evaporation material according to any one of claims 3 to 6, wherein a raw material is melted and cast to form an ingot and the ingot is thereafter subject to a wire drawing process to prepare an evaporation material, or a raw material is melted and thereafter granulated to prepare an evaporation material, wherewith a surface part thereof is cut and removed after the wire drawing process or after the granulation process.~~

~~[Claim 8]~~

~~A method of producing the evaporation material according to any one of claims 3 to 6,~~

~~wherein a raw material is melted and cast to form an ingot and the ingot is thereafter subject to a wire drawing process to prepare an evaporation material, or a raw material is melted and thereafter granulated to prepare an evaporation material, wherewith, after melting the raw material, 0.1 wt% or more of a molten metal thereof is left within a crucible to prepare a cast ingot, or granulated.~~

~~[Claim 9]~~

~~The method of producing the evaporation material according to claim 7 or claim 8, wherein heat treatment is performed before or after and during the wire drawing process.~~